

## **KSA1015**

### **LOW FREQUENCY AMPLIFIER**

- Collector-Base Voltage : V<sub>CBO</sub>= -50V
- Complement to KSC1815



1. Emitter 2. Collector 3. Base

## **PNP Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{CBO}$	Collector-Base Voltage	-50	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-150	mA
I <sub>B</sub>	Base Current	-50	mA
P <sub>C</sub>	Collector Power Dissipation	400	mW
T <sub>J</sub>	Junction Temperature	125	°C
T <sub>ST9</sub>	Storage Temperature	-65 ~ 150	°C

## **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = -100 \mu A, I_E = 0$	-50			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> =0	-50			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -10\mu A, I_C = 0$	-5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = -50V, I <sub>E</sub> =0			-0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ = -5V, $I_{C}$ =0			-0.1	μΑ
h <sub>FE1</sub>	DC Current Gain	$V_{CE}$ = -6V, $I_{C}$ = -2mA	70		400	
$h_{FE2}$		$V_{CE} = -6V, I_{C} = -150 \text{mA}$	25			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA		-0.1	-0.3	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA			-1.1	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = -10V, I <sub>C</sub> =-1mA	80			MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f=1MHz		4	7	pF
NF	Noise Figure	$V_{CE} = -6V, I_{C} = -0.1 \text{mA}$		0.5	6	dB
		f=100Hz, $R_G$ =10k $\Omega$				

## **h**<sub>FE</sub> Classification

Classification	0	Y	GR
h <sub>FE1</sub>	70 ~ 140	120 ~ 240	200 ~ 400

## **Typical Characteristics**

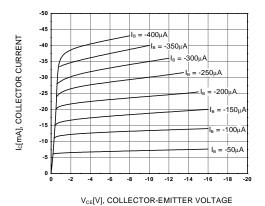


Figure 1. Static Characteristic



V<sub>CE</sub> = -6V

Figure 2. DC current Gain

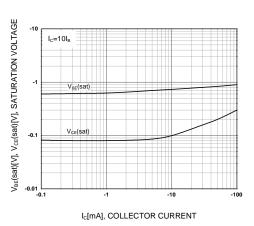


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

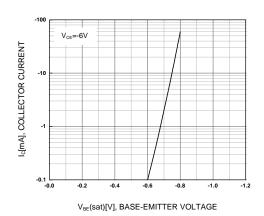


Figure 4. Base-Emitter On Voltage

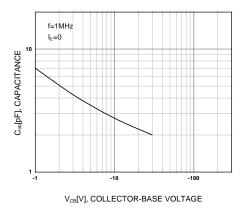


Figure 5. Collector Output Capacitance

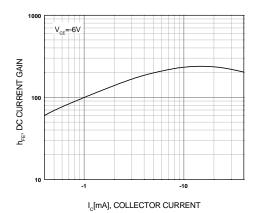
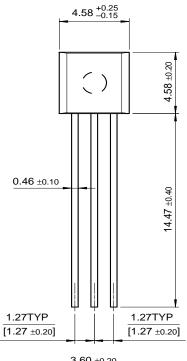


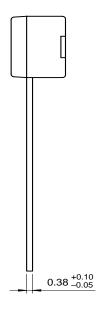
Figure 6. Current Gain Bandwidth Product

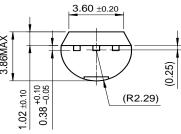
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# **Package Dimensions**

TO-92







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EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
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